

## NPN SILICON POWER TRANSISTORS

...designed for use in power amplifier and switching circuits .

### FEATURES:

\*Collector-Emitter Sustaining Voltage-

$$V_{CEO(sus)} = 100 \text{ V (Min)}$$

\* Collector-Emitter Saturation Voltage -

$$V_{CE(sat)} = 1.0 \text{ V (Max.) @ } I_C = 3.0 \text{ A, } I_B = 0.3 \text{ A}$$

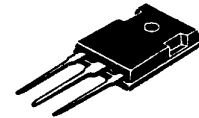
\* Switching Time -  $t_f = 1.0 \text{ us (Max.) @ } I_C = 3.0 \text{ A}$

**NPN**  
**2SC2908**

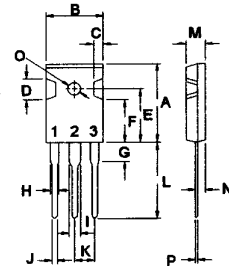
**5.0 AMPERE**  
**SILICON POWER**  
**TRANSISTORS**  
**100 VOLTS**  
**50 WATTS**

### MAXIMUM RATINGS

Characteristic	Symbol	2SC2908	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	V
Collector-Base Voltage	$V_{CBO}$	200	V
Emitter-Base Voltage	$V_{EBO}$	12	V
Collector Current - Continuous - Peak	$I_C$ $I_{CM}$	5.0 10	A
Base current	$I_B$	2.5	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	50 0.4	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$



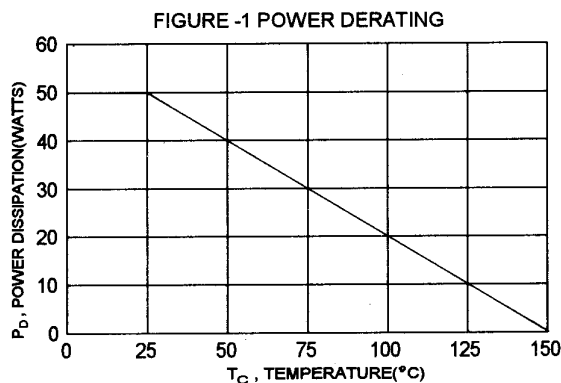
**TO-247(3P)**



PIN 1.BASE  
2.COLLECTOR  
3.EMITTER

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	2.5	$^\circ\text{C/W}$



DIM	MILLIMETERS	
	MIN	MAX
A	20.63	22.38
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.81	15.22
F	11.72	12.84
G	4.20	4.50
H	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.26	5.66
L	18.50	21.50
M	4.68	5.36
N	2.40	2.80
O	3.25	3.65
P	0.55	0.70

**ELECTRICAL CHARACTERISTICS (  $T_c = 25^\circ\text{C}$  unless otherwise noted )**

Characteristic	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Sustaining Voltage ( $I_C = 3.0\text{A}$ , $I_{B1} = 0.3\text{A}$ , $L = 1.0\text{mH}$ )	$V_{CE(sus)}$	100		V
Collector Cutoff Current ( $V_{CE} = 100\text{V}$ , $V_{BE(OFF)} = -1.5\text{V}$ )	$I_{CEX}$		10	$\mu\text{A}$
Collector Cutoff Current ( $V_{CB} = 100\text{V}$ , $I_E = 0$ )	$I_{CBO}$		10	$\mu\text{A}$
Emitter Cutoff Current ( $V_{EB} = 5.0\text{V}$ , $I_C = 0$ )	$I_{EBO}$		10	$\mu\text{A}$

**ON CHARACTERISTICS (1)**

DC Current Gain ( $I_C = 0.3\text{A}$ , $V_{CE} = 5.0\text{V}$ ) * ( $I_C = 3.0\text{A}$ , $V_{CE} = 5.0\text{V}$ )	$hFE(2)$ $hFE$	60 40	320	
Collector-Emitter Saturation Voltage ( $I_C = 3.0\text{A}$ , $I_B = 300\text{mA}$ )	$V_{CE(sat)}$		1.0	V
Base-Emitter Saturation Voltage ( $I_C = 3.0\text{A}$ , $I_B = 300\text{mA}$ )	$V_{BE(sat)}$		1.5	V

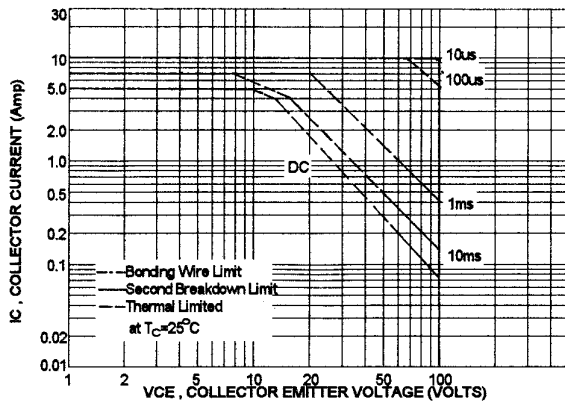
**SWITCHING CHARACTERISTICS**

Turn-on Time	$V_{CC} = 30\text{V}$ , $I_C = 3.0\text{A}$ $I_{B1} = -I_{B2} = 300\text{mA}$ $R_L = 10\text{ohm}$	$t_{on}$	0.5	$\mu\text{s}$
Storage Time		$t_s$	2.0	$\mu\text{s}$
Fall Time		$t_f$	1.0	$\mu\text{s}$

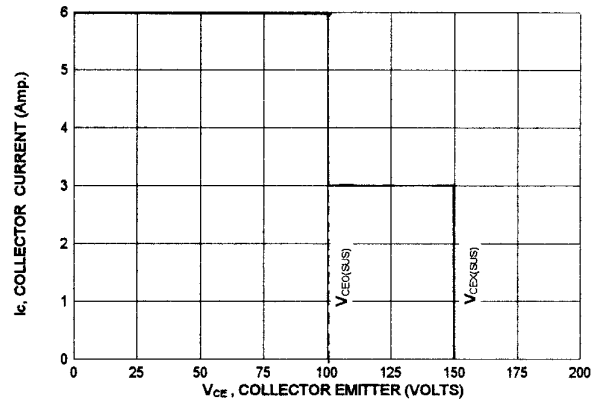
(1) Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ \*  $hFE(2)$  Classification :

60	M	120	100	L	200	160	K	320
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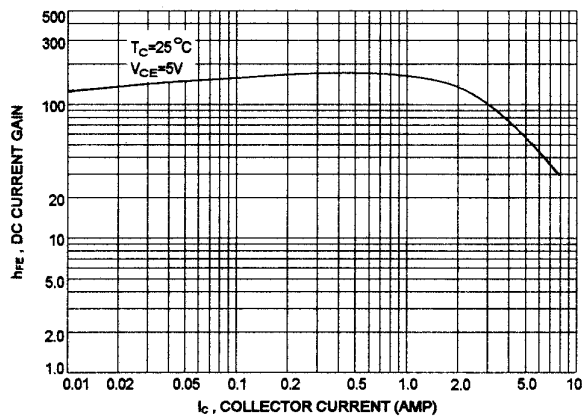
SAFE OPERATING AREA



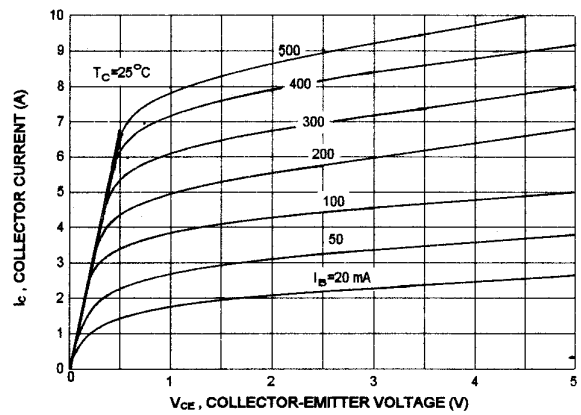
REVERSE BIASE SAFE OPERATING AREA



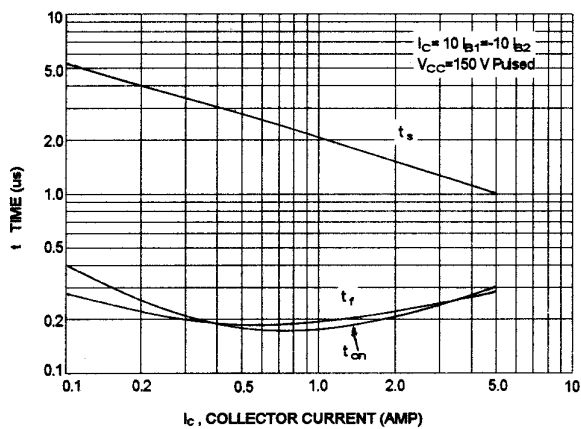
DC CURRENT GAIN



IC - Vce



SWITCHING TIME



"ON" VOLTAGES

